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U.S. Department of Commerce, Patent and Trademark		Atty. Docket No.		Application No.				
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		SNDK.211US0 (formerly M-10311 US).		<del>09/793,370</del>				
		Applicants		10/804,770				
(Use several sheets if necessary)		Geoffrey Gongwer and Daniel Guterman						
		Filing Date		Group				
		<del>February 26, 2001</del> March 19, 2004		2825				
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
ADM	1	4,628,487	Dec. 9, 1986	Smayling	—	—		
ADM	2	5,422,842	Jun. 6, 1995	Cerne et al.	—	—		
ADM	3	5,557,567	Sep. 17, 1996	Bergemont et al.	—	—		
ADM	4	5,796,652	Aug. 18, 1998	Takeshima et al.	—	—		
ADM	5	6,014,330	Jan. 11, 2000	Endoh et al.	—	—		
ADM	6	6,134,148	Oct. 17, 2000	Kawahara et al.	—	—		
ADM	7	6,266,270 B1	Jul. 24, 2001	Nobukata	—	—		
U.S. Published Patent Application Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
Foreign Patent Documents								
						Translation		
		Document	Date	Country	Class	Subclass	Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
ADM	8	Chi, Min-hwa et al., "Low-Voltage Multi-level Flash Memory: Determination of Minimum Spacing Between Multi-levels," Semiconductor Electronics, 1996, ICSE 1996 Proceedings, 1996 IEEE International Conference Penang, Malaysia, November 26, 1996, pages 1-5.						
ADM	9	Chi, Min-hwa et al., "Multi-level Flash/EPROM Memories: New Self-convergent Programming Methods for Low-voltage Applications," Electron Devices Meeting, December 10, 1995, pp. 271-274.						
ADM	10	Ohkawa, Masayoshi et al., "A 98mm <sup>2</sup> 3.3V 64Mb Flash Memory with FN-NOR Type 4-level Cell," IEEE International Solid-State Circuits Conference, February 8, 1996, pp. 36-37 and 413.						
ADM	11	International Search Report in counterpart PCT application PCT/US02/05265, Dec. 3, 2002, 5pages.						
Examiner <u>ADM</u>		Date Considered <u>8/5/2004</u>						
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								

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	M-10311 US	<del>09/793,370</del> 7
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicants	10/804,770
(Use several sheets if necessary)	Gongwer et al.	
	Filing Date March 19, 2004	Group
	February 26, 2001	2825

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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ABM	AB	5,623,436	4/22/97	Sowards et al.	365	.45	
ABM	AC	5,677,869	10/14/97	Fazio et al.	365	185.03	
ABM	AD	5,729,489	3/17/98	Fazio et al.	365	185.03	
ABM	AE	5,754,470	5/19/98	Engl et al.	365	185.03	
ABM	AF	5,768,192	6/16/98	Eitan	365	185.24	
ABM	AG	5,784,315	7/21/98	Itoh	365	185.22	
ABM	AH	5,801,989	9/1/98	Lee et al.	365	185.22	
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## Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	AN							
	AO							
	AP							

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AQ	
	AR	
	AS	

Examiner ABM Date Considered 8/5/2004

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